


[Home](#) > [2N6372 \(#23578\)](#)

2N6372 (#23578)

Products

- ▶ [Product Directory](#)
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- ▶ [Parametric Search](#)

Overview

Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			1.00	V
DC Current Gain	HFE	20.00		100.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	$V_{BR(CBO)}$			90.00	V
Collector Current (dc)	I_C			6.00	A
Collector-Emitter Voltage (Base Open)	V_{CEO}			80.00	V
Emitter-Base Voltage (Collector Open)	V_{EBO}			6.00	V
Power Dissipation, Total	P_T			40.00	W

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